

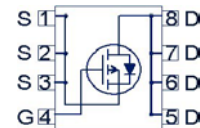
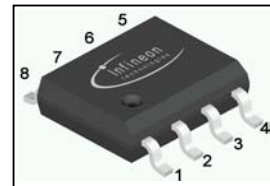
**OptiMOS<sup>®</sup>-P Power-Transistor**
**Features**

- P-Channel
- Enhancement mode
- Logic level
- 150°C operating temperature
- Avalanche rated
- Qualified according JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$		-30	V
$R_{DS(on),max}$	$V_{GS}= 10\text{ V}$	8.0	m $\Omega$
	$V_{GS}= 4.5\text{ V}$	12.0	A
$I_D$		-14.9	A

PG-DSO-8



Type	Package	Marking	Leadfree	Halogen free	packing
BSO301SP H	PG-DSO-8	301SP	Yes	Yes	dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value		Unit
			≤10 secs	steady state	
Continuous drain current	$I_D$	$T_A=25\text{ °C}^{1)}$	-14.9	-12.6	A
		$T_A=70\text{ °C}^{1)}$	-11.9	-10	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}^{2)}$	-60		
Avalanche energy, single pulse	$E_{AS}$	$I_D=-14.9\text{ A}, R_{GS}=25\ \Omega$	248		mJ
Gate source voltage	$V_{GS}$		±20		V
Power dissipation	$P_{tot}$	$T_A=25\text{ °C}^{1)}$	2.5	1.79	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150		°C
ESD class		JESD22-A114 HBM	1C (1kV - 2kV)		
Soldering temperature			260		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - soldering point	$R_{thJS}$		-	-	35	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , $t_p \leq 10$ s	-	-	50	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , steady state	-	-	80	

**Electrical characteristics, at  $T_j=25$  °C, unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0$ V, $I_D=-250$ $\mu$ A	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=-250$ $\mu$ A	-1	-1.5	-2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-30$ V, $V_{GS}=0$ V, $T_j=25$ °C	-	-0.1	-1	$\mu$ A
		$V_{DS}=-30$ V, $V_{GS}=0$ V, $T_j=125$ °C	-	-10	-100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=-20$ V, $V_{DS}=0$ V	-	-10	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-4.5$ V, $I_D=-12$ A	-	8.8	12	m $\Omega$
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10$ V, $I_D=-14.9$ A	-	6.3	8.0	
Transconductance	$g_{fs}$	$ V_{DS}  > 2 I_D  R_{DS(on)max}$ , $I_D=-14.9$ A	22	44	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu$ m thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V},$ $V_{DS}=-25\text{ V}, f=1\text{ MHz}$	-	4430	5890	pF
Output capacitance	$C_{oss}$		-	1180	1570	
Reverse transfer capacitance	$C_{rss}$		-	970	1500	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V},$ $V_{GS}=-10\text{ V},$ $I_D=-1\text{ A}, R_G=6\ \Omega$	-	15	23	ns
Rise time	$t_r$		-	22	33	
Turn-off delay time	$t_{d(off)}$		-	130	195	
Fall time	$t_f$		-	110	165	

**Gate Charge Characteristics<sup>3)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=-24\text{ V},$ $I_D=-14.9\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	-11	-15	nC
Gate charge at threshold	$Q_{g(th)}$		-	-7.1	-9.5	
Gate to drain charge	$Q_{gd}$		-	-35		
Switching charge	$Q_{sw}$		-	-40	-59	
Gate charge total	$Q_g$		-	-102	-136	
Gate plateau voltage	$V_{plateau}$		-	-2.5	-	V
Output charge	$Q_{oss}$	$V_{DD}=-15\text{ V}, V_{GS}=0\text{ V}$	-	-36	-48	

**Reverse Diode**

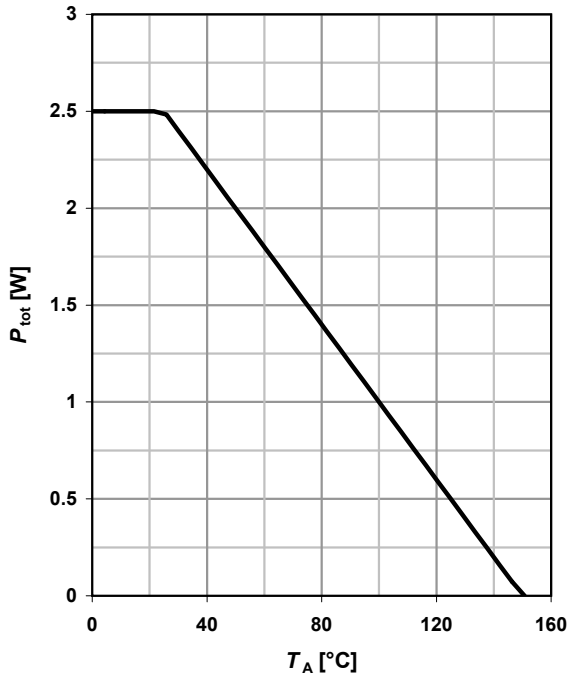
Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	-2.1	A
Diode pulse current	$I_{S,pulse}$		-	-	-60	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-14.9\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-0.82	-1.2	V
Reverse recovery time	$t_{rr}$	$V_R=15\text{ V}, I_F=-14.9\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	32	40	ns
Reverse recovery charge	$Q_{rr}$		-	-20	-25	nC

<sup>2)</sup> See figure 3

<sup>3)</sup> See figure 16 for gate charge parameter definition

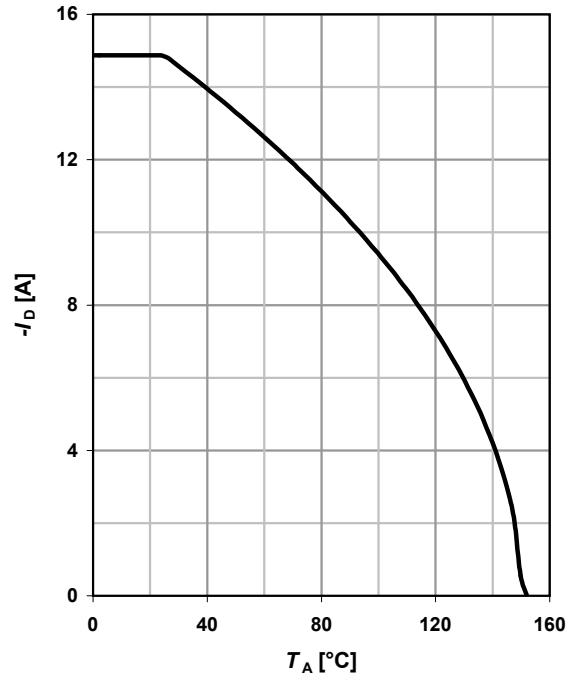
**1 Power dissipation**

$P_{tot}=f(T_A); t_p \leq 10 \text{ s}$



**2 Drain current**

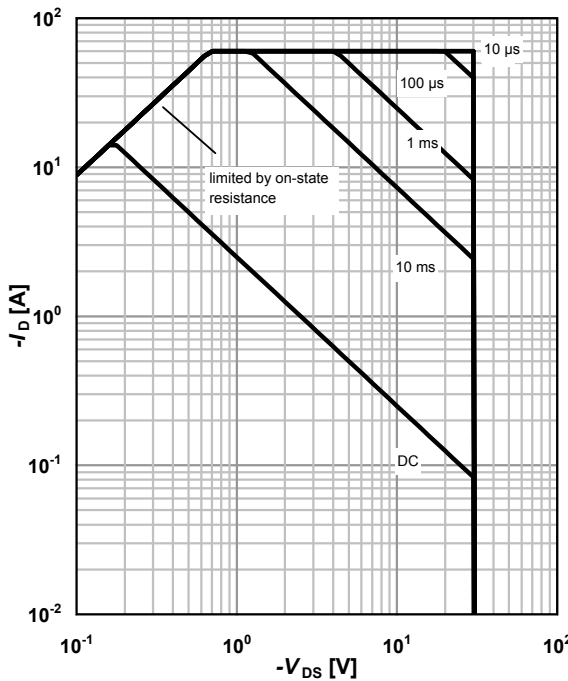
$I_D=f(T_A); |V_{GS}| \geq 10 \text{ V}; t_p \leq 10 \text{ s}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25 \text{ °C}^1; D=0$

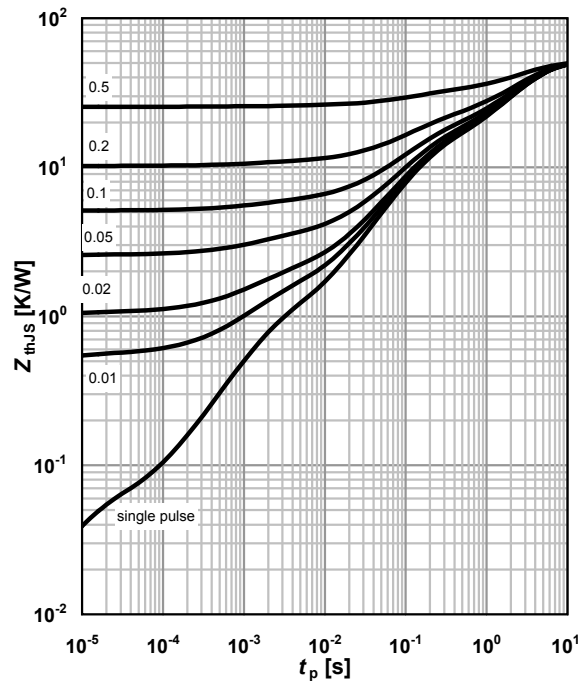
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJS}=f(t_p)$

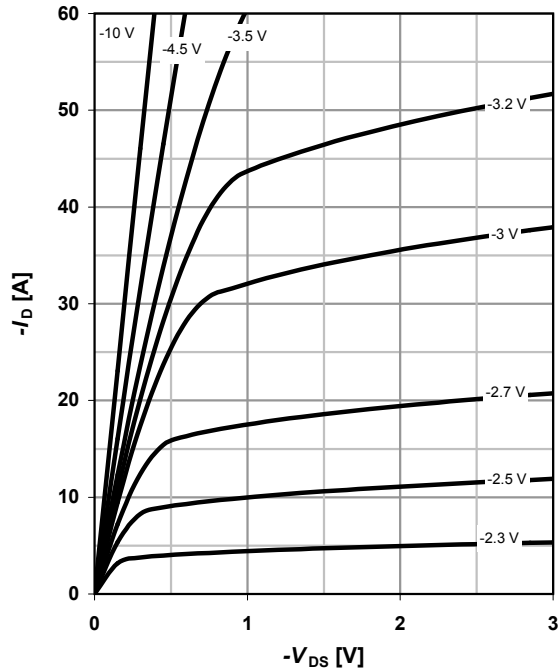
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

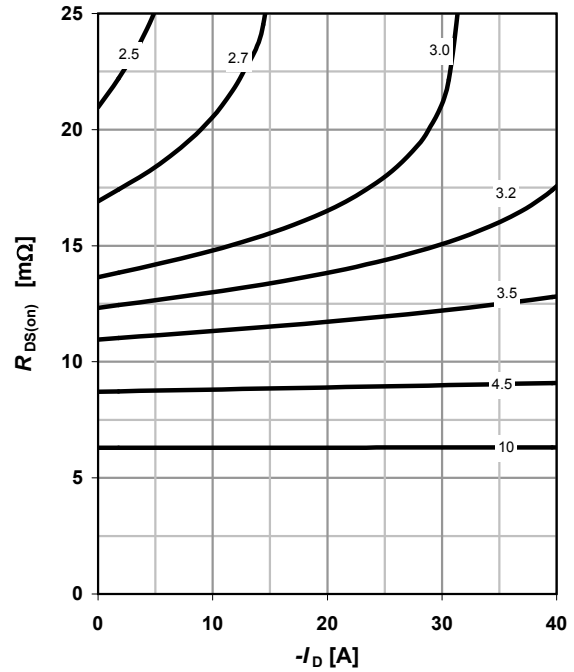
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

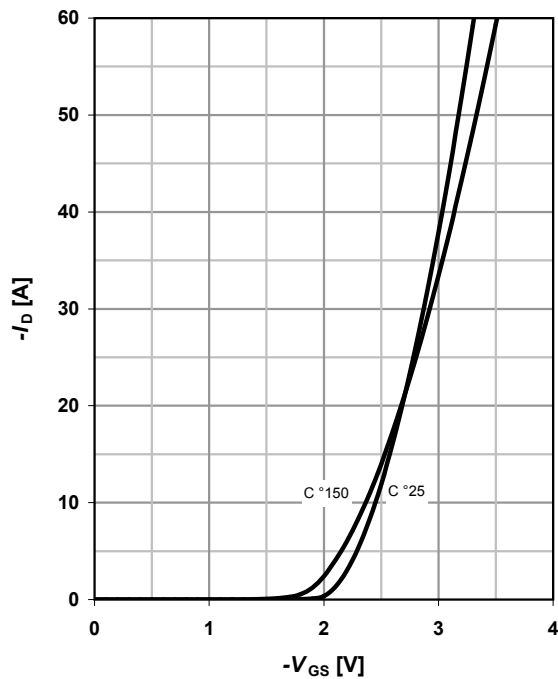
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

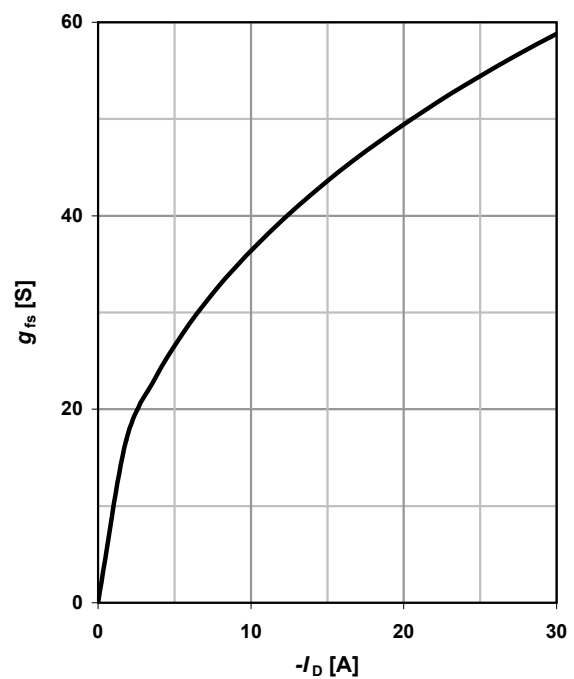
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



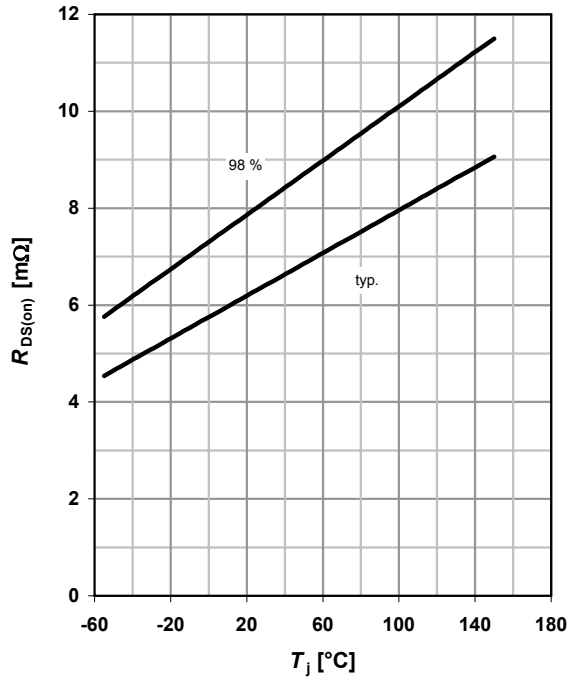
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



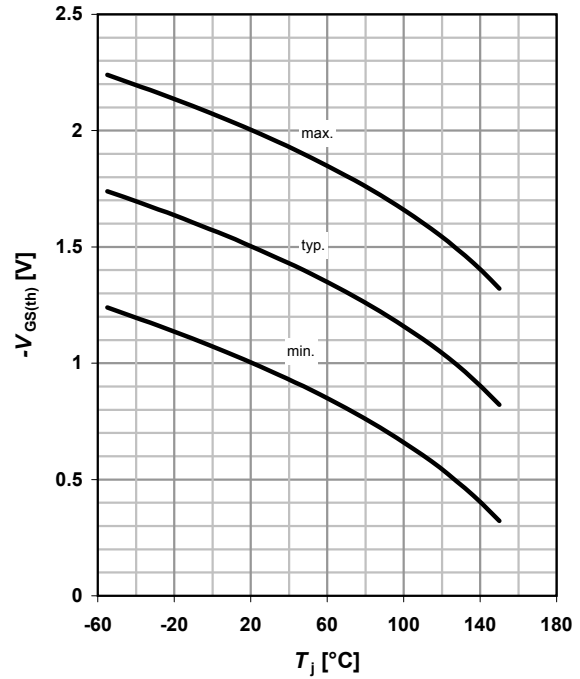
**9 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j); I_D = -14.9 \text{ A}; V_{GS} = -10 \text{ V}$



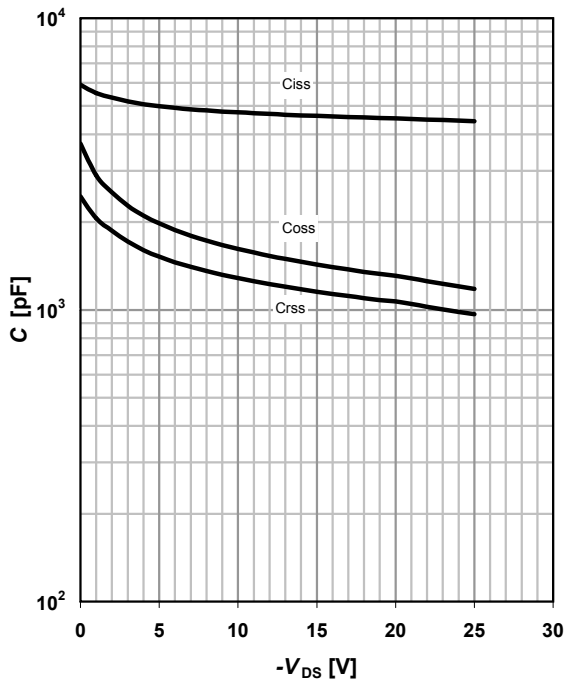
**10 Typ. gate threshold voltage**

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -250 \mu\text{A}$



**11 Typ. capacitances**

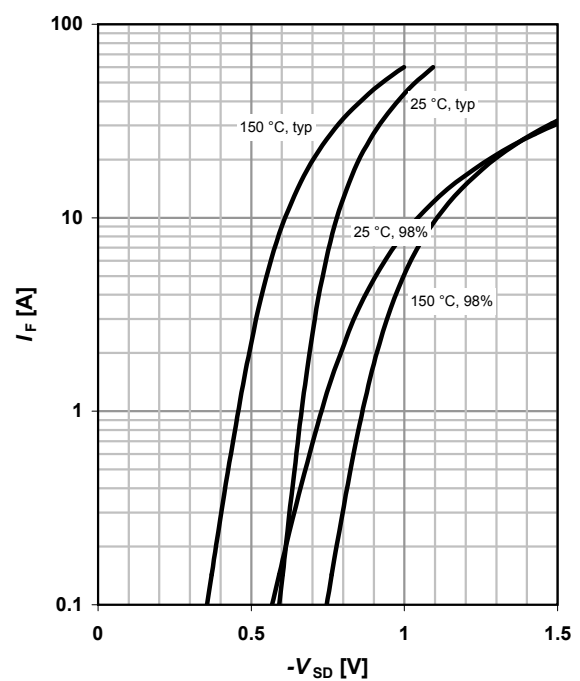
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

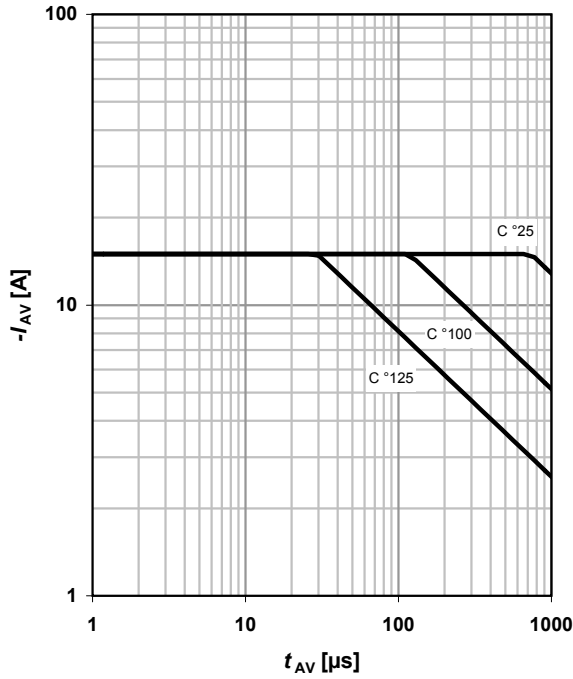
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$

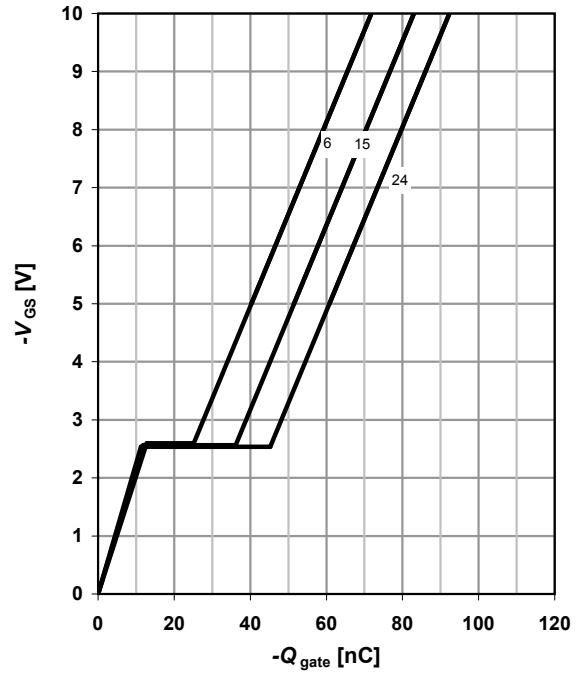
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

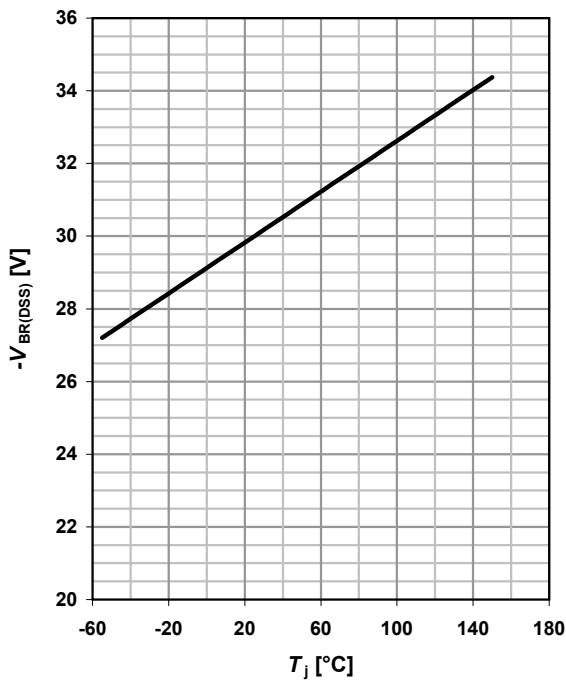
$V_{GS}=f(Q_{gate}); I_D=-14.9\ A\ pulsed$

parameter:  $V_{DD}$



**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=-250\ \mu A$

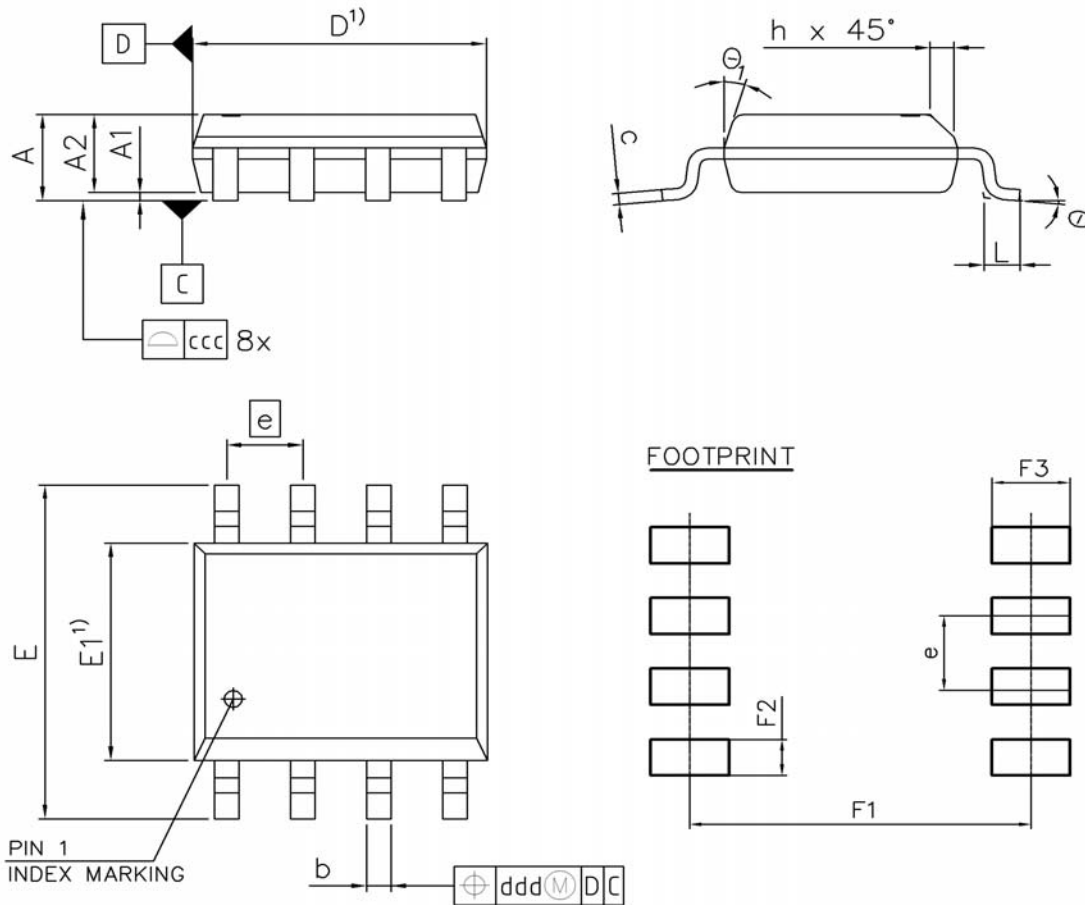


**16 Gate charge waveforms**



Package Outline

P-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
θ	0°	8°	0°	8°
θ <sub>1</sub>	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

DOCUMENT NO.  
Z8B00003333

SCALE

EUROPEAN PROJECTION

ISSUE DATE  
09.01.2008

REVISION  
02



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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